

DUAL P-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

Product Summary

V _{(BR)DSS}	R _{DS(on) max}	I _D T _A = +25°C
-30V	45mΩ @ V _{GS} = -10V	-6.9A
	65mΩ @ V _{GS} = -4.5V	-5.1A

Description

This new generation MOSFET has been designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

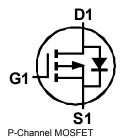
- Power Management Functions
- Backlighting
- DC-DC Converters

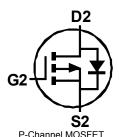
Features

- Dual P-Channel MOSFET
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin annealed over Copper lead frame. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.072g (approximate)





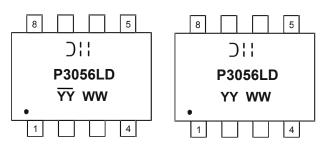
Ordering Information (Note 4)

Part Number	Case	Packaging
DMP3056LSD-13	SO-8	2,500/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



Shanghai A/T Site

DII = Manufacturer's Marking
P3056LD = Product Type Marking Code
YYWW = Date Code Marking
YY or YY = Year (ex: 14 = 2014)
WW = Week (01 - 53)

YY = Date Code Marking for SAT (Shanghai Assembly/ Test site)
YY = Date Code Marking for CAT (Chengdu Assembly/ Test site)

Chengdu A/T Site



Characteristic			Symbol	Value	Units
Drain-Source Voltage		V_{DSS}	-30	V	
Gate-Source Voltage		V _{GSS}	±20	V	
Drain Current (Note 5)	Steady State	T _A = +25°C T _A = +70°C	I _D	-6.9 -5.8	А
Pulsed Drain Current (Note 6)			I _{DM}	-24	A

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P _D	2.5	W
Thermal Resistance, Junction to Ambient (Note 5)	$R_{ heta JA}$	50	°C/W
Operating and Storage Temperature Range	T _{J,} T _{STG}	-55 to +150	°C

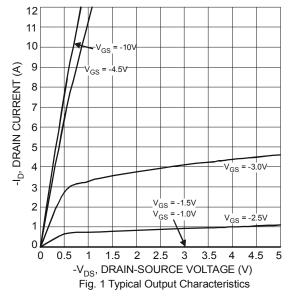
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Cumhal	Min	T	Moss	11!4	Took Condition	
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)	5.7		1	1		Tr. 2011 272 1	
Drain-Source Breakdown Voltage	BV _{DSS}	-30			V	$V_{GS} = 0V, I_D = -250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}			-1	μA	$V_{DS} = -30V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
Gate-Gource Leakage	IGSS			±800		$V_{GS} = \pm 25V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(th)}	-1	-1.7	-2.1	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
Static Drain-Source On-Resistance			_	45		$V_{GS} = -10V, I_D = -6.0A$	
Static Drain-Source On-Resistance	R _{DS (ON)}	_	_	65	mΩ	$V_{GS} = -4.5V, I_{D} = -5.0A$	
Forward Transconductance	9fs	_	8	_	S	V _{DS} = -10V, I _D = -5.3A	
Diode Forward Voltage (Note 7)	V_{SD}	-0.5	_	-1.2	V	V _{GS} = 0V, I _S = -1.7A	
DYNAMIC CHARACTERISTICS						•	
Input Capacitance	C _{iss}	_	722	_	pF		
Output Capacitance	Coss	_	114	_	pF	$V_{DS} = -25V, V_{GS} = 0V$	
Reverse Transfer Capacitance	C _{rss}	_	92	_	pF	f = 1.0MHz	
Gate Resistance	R_{G}	_	3.3	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$ f = 1.0MHz	
SWITCHING CHARACTERISTICS						•	
	Q_G	_	6.8	_	nC	$V_{DS} = -15V, V_{GS} = -4.5V,$	
Total Gate Charge			13.7			I _D = -6A	
0.4.0	Q _G					$V_{DS} = -15V$, $V_{GS} = -10V$, $I_{D} = -6A$	
Gate-Source Charge	Q _{GS}		1.6	_	nC		
Gate-Drain Charge	Q_GD	_	4.2	_		D -	
Turn-On Delay Time	t _{d(on)}	_	6.4				
Rise Time	t _r	_	5.3	_	ns	$V_{DS} = -15V, V_{GS} = -10V,$	
Turn-Off Delay Time	t _{d(off)}	_	26.5	_	115	$I_D = -1A, R_G = 6.0\Omega$	
Fall Time	t _f	_	14.7	_			

5. Device mounted on 2 oz. 1" x 1" Copper pads on 2" x 2" FR-4 PCB. 6. Pulse width \leq 10 μ S, Duty Cycle \leq 1%. Notes:

7. Short duration pulse test used to minimize self-heating effect.





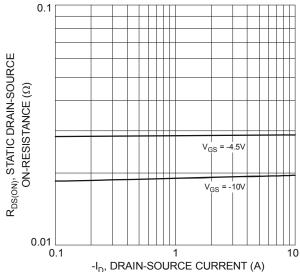
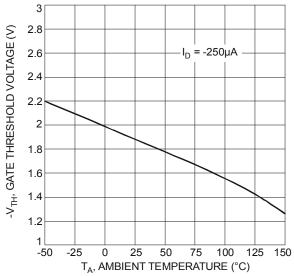
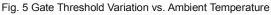
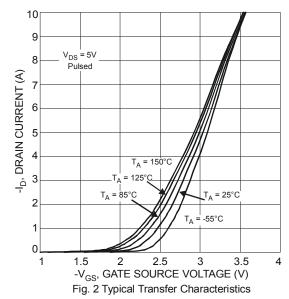


Fig. 3 On-Resistance vs. Drain Current & Gate Voltage







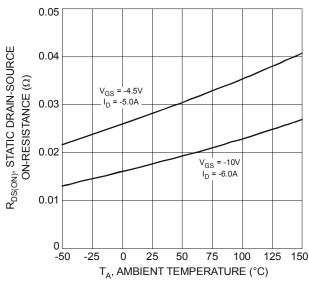
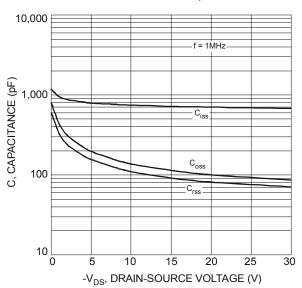
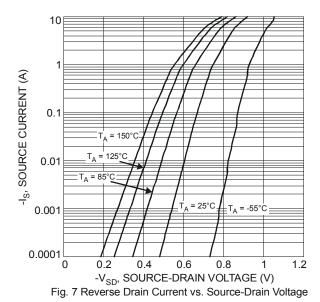


Fig. 4 Static Drain-Source On-Resistance vs. Ambient Temperature

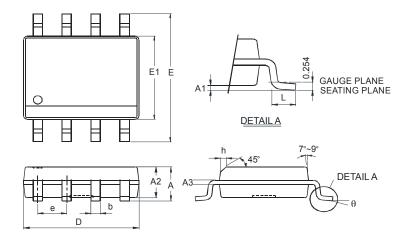






Package Outline Dimensions

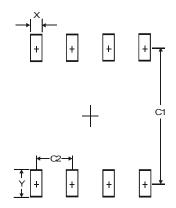
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



SO-8				
Dim	Min	Max		
Α	-	1.75		
A 1	0.10	0.20		
A2	1.30	1.50		
A3	0.15	0.25		
b	0.3	0.5		
D	4.85	4.95		
Е	5.90	6.10		
E1	3.85	3.95		
е	1.27 Typ			
h	-	0.35		
٦	0.62	0.82		
θ	0°	8°		
All Dimensions in mm				

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
X	0.60
Υ	1.55
C1	5.4
C2	1.27



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